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Erratum: “The effects of wetting layer on electronic and optical properties of intersubband P-to-S transitions in strained dome-shaped InAs/GaAs quantum dots” [AIP Advances 4, 067113 (2014)] **FREE**

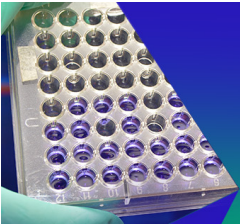
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Erratum: “The effects of wetting layer on electronic and optical properties of intersubband P-to-S transitions in strained dome-shaped InAs/GaAs quantum dots” [AIP Advances 4, 067113 (2014)]

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Reference 68 erroneously attributed the submitted paper cited to Optics Express. The paper, “Investigation of in-plane- and z-polarized intersubband transitions in pyramid-shaped InAs/GaAs quantum dots coupled to wetting layer: Size and shape matter” by Mohammad Sabaieian and Mohammadreza Shahzadeh, is published in the Journal of Applied Physics.¹

¹M. Sabaieian and M. Shahzadeh, “Investigation of in-plane-and z-polarized intersubband transitions in pyramid-shaped InAs/GaAs quantum dots coupled to wetting layer: Size and shape matter,” *Journal of Applied Physics* **116**, 043102 (2014).

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